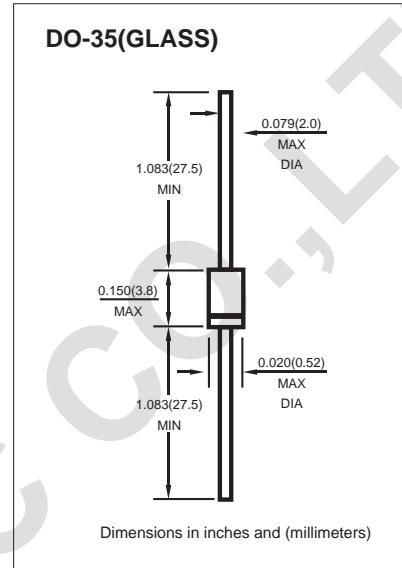


SILICON BIDIRECTIONAL DIAC

FEATURE

The three layer ,two terminal,axial lead,hermetically sealed diacs are designed specifically for triggering thyristors.They demonstrate low breakover current at breakover voltage as they withstand peak pulse current The breakover symmetry is within three volts(DB3,DC34,DB4)or four volts(DB6).These diacs are intended for use in thyrisitors phase control,circuits for lamp dimming.universal motor speed control, and heat control.

JF S DB3/DC34/DB4/DB6 are bi-directional triggered diode designed to operate in conjunction with Triacs and SCR's



ABSOLUTE RATINGS(LIMITING VALUES)

Symbols	Parameters	Value				Units
		DB3	DC34	DB4	DB6	
P _c	Power Dissipation on printed Circuit(L=10mm)	T _A = 50 °C 150				mW
I _{TRM}	Repetitive peak on-state Current	t _p =10μs F=100Hz		2.0	2.0	2.0
				16		A
T _{STG/T_J}	Storage and Operating Junction Temperature	-40 to +125/-40 to 110				°C

ELECTRICAL CHARACTERISTICS

Symbols	Parameters	Test Conditions	Value				Units
			Min	28	30	35	
V _{BO}	Breakover Voltage(Note2) See diagram 1	C=22nF(Note2) See diagram 1	Typ	32	34	40	60
			Max	36	38	45	70
							V
I _{+V_{BO}} -I _{-V_{BO}}	Breakover Voltage Symmetry	C=22nF(Note2) See diagram 1	Max	± 3			± 4
I _{+ΔV_I}	Dynamic Breakover Voltage(Note 1)	ΔI=(I _{so} to I _F =10mA) See Diagram 1	Min	5			10
V _O	Output Voltage (Note 1)	See Diagram 2	Min	5			V
I _{BO}	Breakwver Current(Note 1)	C=22nF(Note2)	Max	100			μA
t _r	Rise Time (Note1)	See Diagram 3	Tip	1.5			μS
I _B	Leakage Current(Note1)	V _B =0.5V _{BO} max see diagrom1	Max	10			μA

Notes:1.Electrical characteristics applicable in both forward and reverse direclions.

2.Connected in parallel with the devices.

DIAGRAM1: Current-voltage characteristics

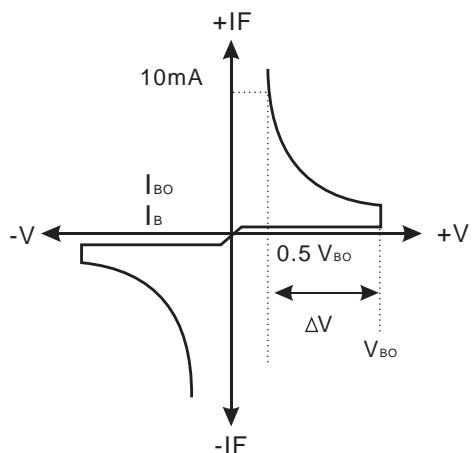


DIAGRAM2 : Test circuit for output voltage

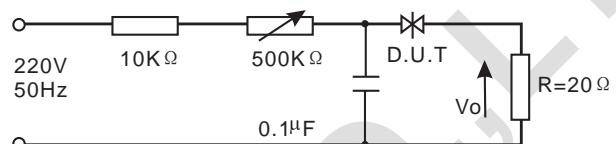


DIAGRAM3 : Test circuit see diagram2 adjust R for $I_P=0.5\text{A}$

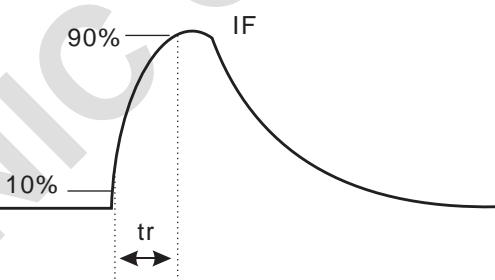


FIG.1-Power dissipation versus ambient temperature (maximum values)

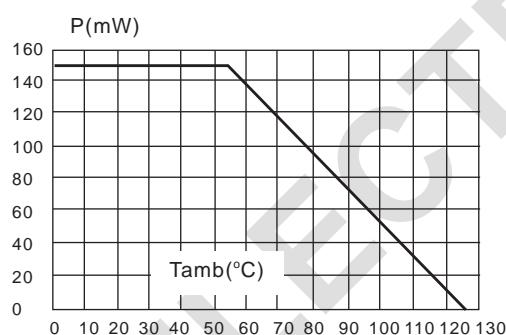


FIG.3-Peak pulse current versus pulse duration (maximum values)

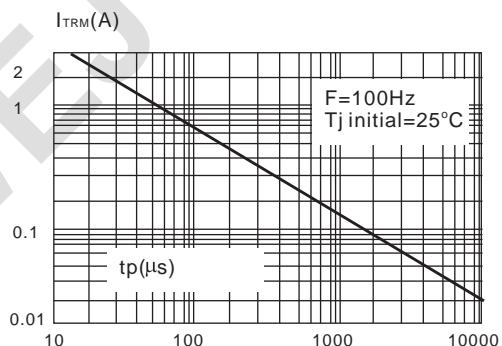


FIG.2-Relative variation of V_{BO} versus junction temperature (typical values)

